COMPLIANT



Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 90 A



PRIMARY CHARACTERISTICS					
V_{R}	1200 V				
V _F (typical)	2.46 V				
t _{rr} (typical)	35 ns				
I _{F(AV)} per module at T _C	90 A at 63 °C				
Package	SOT-227				

FEATURES

- Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996



DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA90FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 Gen 2 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode breakdown voltage	V _R		1200	V	
Continuous forward current, per leg	I _F	T _C = 83 °C	45	۸	
Single pulse forward current, per leg	I _{FSM}	T _J = 25 °C	400	Α	
Martin and a district all and a second	P _D	T _C = 83 °C	139	W	
Maximum power dissipation, per leg		T _C = 100 °C	104		
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIO	NS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100 \mu A$		1200	-	-	
		I _F = 25 A		-	2.46	3.0	V
	V_{FM}	I _F = 40 A	See fig. 1	-	2.68	3.3	
Famuerd voltage		I _F = 25 A, T _J = 125 °C		-	2.22	-	
Forward voltage		I _F = 40 A, T _J = 125 °C		-	2.52	-	
		I _F = 25 A, T _J = 150 °C		-	2.12	2.55	
		I _F = 40 A, T _J = 150 °C		-	2.43	2.96	
		$V_R = V_R$ rated		-	1.5	75	μA
Reverse leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{ rated}$	See fig. 2	-	0.5	2	A
		T _J = 150 °C, V _R = V _R rated		-	2	5	mA
Junction capacitance	C _T	V _R = 1200 V	See fig. 3	-	30	-	pF



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35	-	
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 40 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	80	-	ns
		T _J = 125 °C		-	130	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	6.8	-	Α
		T _J = 125 °C		-	11.5	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	270	-	nC
		T _J = 125 °C		-	740	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	Ъ		-	-	0.48	
Junction to case, both legs conducting	R_{thJC}		-	-	0.24	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SOT-227		

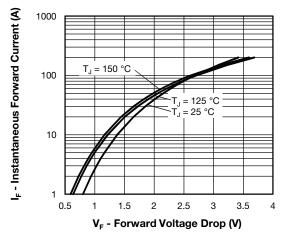


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

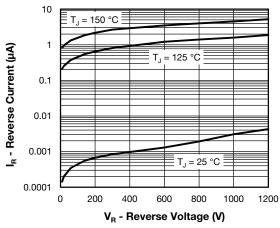


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



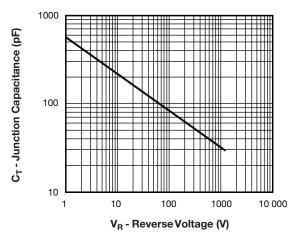


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

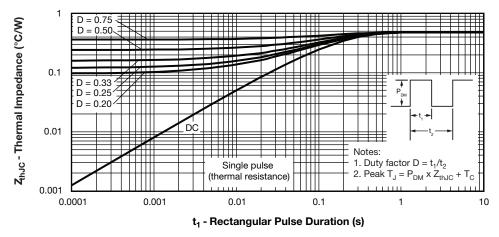


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

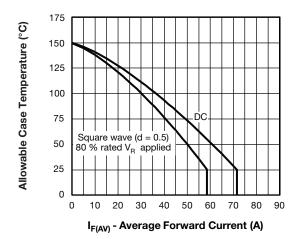


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

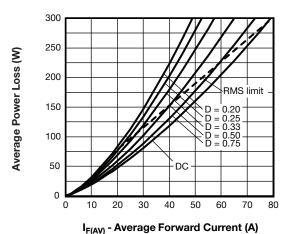
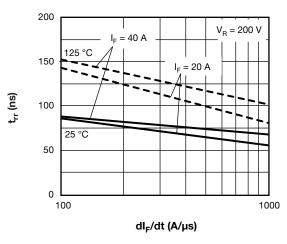


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

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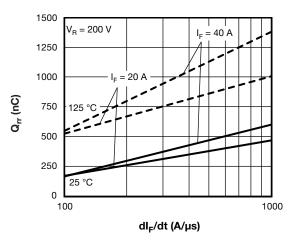


Fig. 8 - Typical Stored Charge vs. dl_F/dt

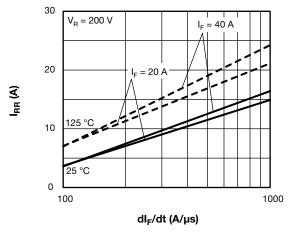


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

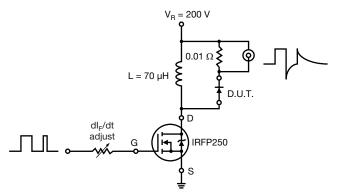
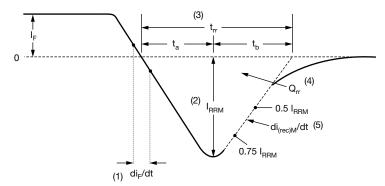


Fig. 10 - Reverse Recovery Parameter Test Circuit

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

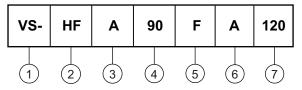
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- HEXFRED® family
- Process designator (A = electron irradiated)
- **4** Average current (90 = 90 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (120 = 1200 V)

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
		Lead Assignment			
two separate diodes, parallel pin-out	F				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				



Legal Disclaimer Notice

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